D1MND9P0

40V N-Channel MOSFETs

BV_{DSS}	$R_{DS(ON)}$	I_D
40 V	9 mΩ	80 A

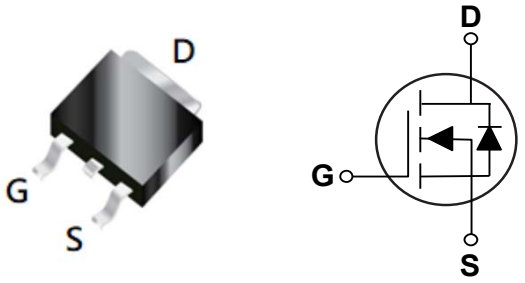
General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- $R_{DS(ON)} \leqq 9m\Omega @ V_{GS}=10V$
- Improved dv/dt Capability
- Fast Switching
- Green Device Available

TO-252 Pin Configuration



Applications

- Battery Protection
- Load Switch
- Uninterruptible Power Supply

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current - Continuous (T_C=25°C)	80	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	200	A
P_D	Power Dissipation (T_C=25°C)	33.7	W
EAS	Single Pulse Avalanche Energy (NOTE 2)	12.8	mJ
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		ND9P0	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	3.7	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=25A	---	---	9	mΩ
		V_{GS}=4.5V , I_D=15A	---	---	12	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250uA	1.2	---	2.5	V
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	22	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{DS}=20V , V_{GS}=10V , I_D=25A	---	37	---	nC
Q_{gs}	Gate-Source Charge		---	6	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=30V , V_{GS}=10V , R_{GEN}=1Ω , I_D=25A	---	12	---	nS
T_r	Rise Time		---	12	---	
$T_{d(off)}$	Turn-Off Delay Time		---	38	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	2400	---	pF
C_{oss}	Output Capacitance		---	192	---	
C_{rss}	Reverse Transfer Capacitance		---	165	---	
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	---	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	50	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A	---	---	1.2	V

NOTES：

1. Repetitive Rating：Pulsed width limited by maximum junction temperature.
2. V_{DD}=36V, V_{GS}=10V, L=0.1mH, I_{AS}=16A.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

Characteristics Curves

FIG. 1-Output Characteristics

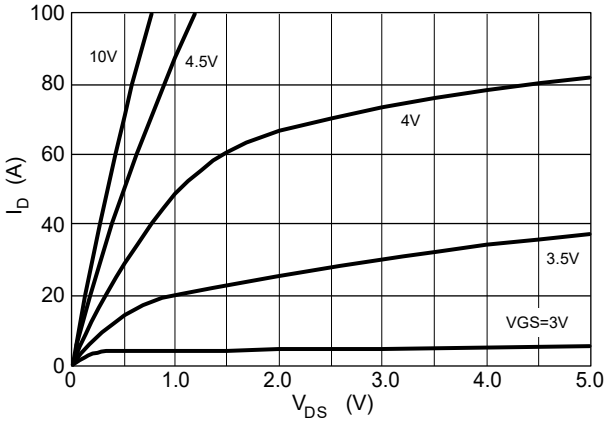


FIG. 2-$R_{DS(ON)}$ vs. I_D

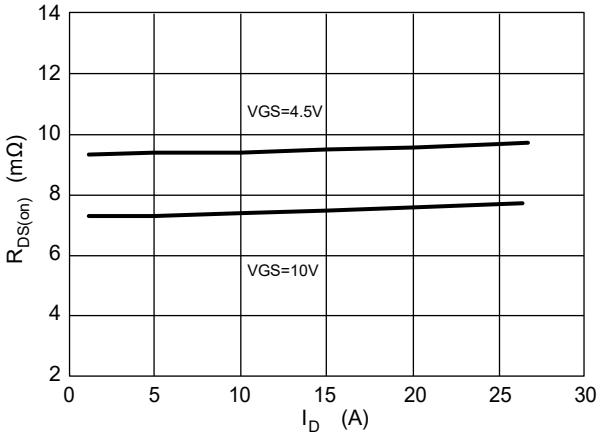


FIG. 3-Normalized BV_{DSS} vs. T_J

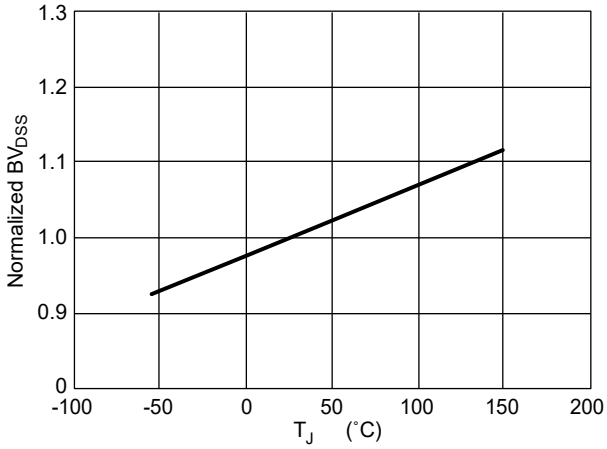


FIG. 4-Normalized $R_{DS(ON)}$ vs. T_J

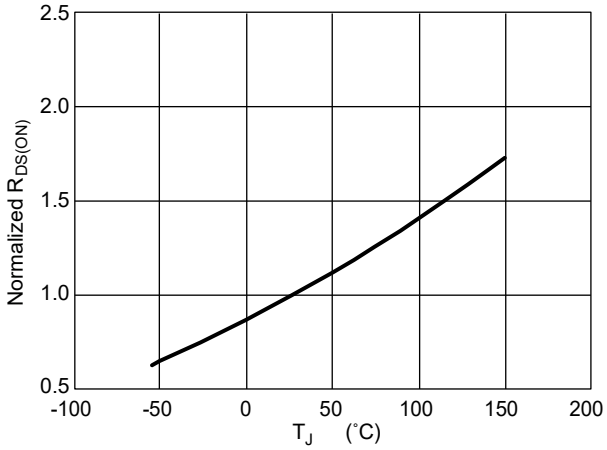


FIG. 5-I_S vs. V_{SD}

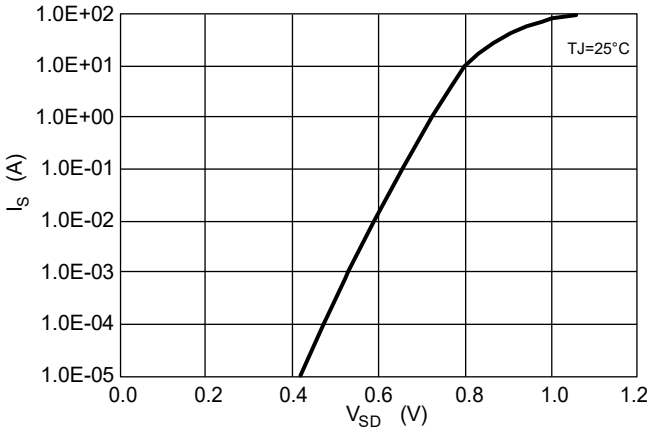
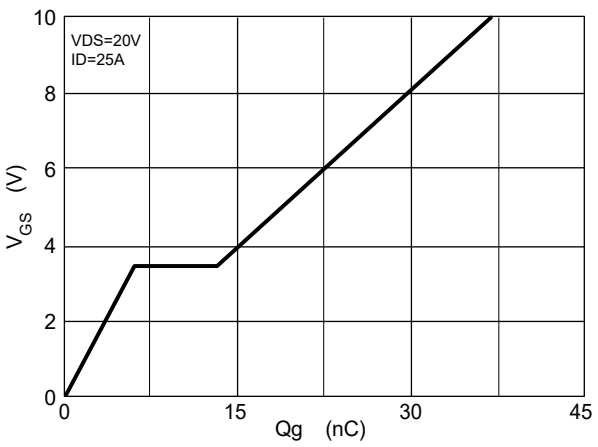


FIG. 6-Gate Charge Characteristics



Characteristics Curves

FIG. 7-Gate Charge Waveform

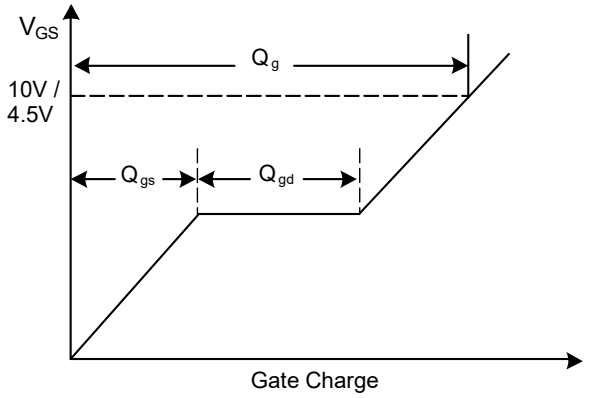
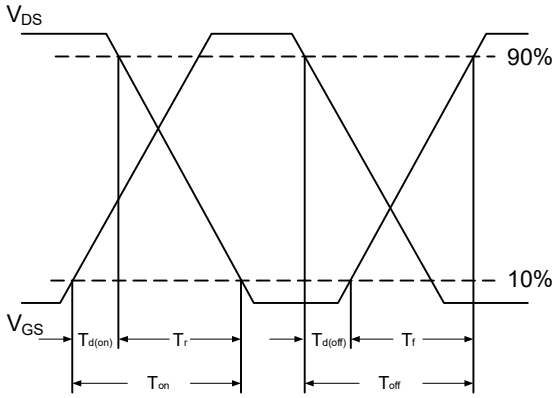
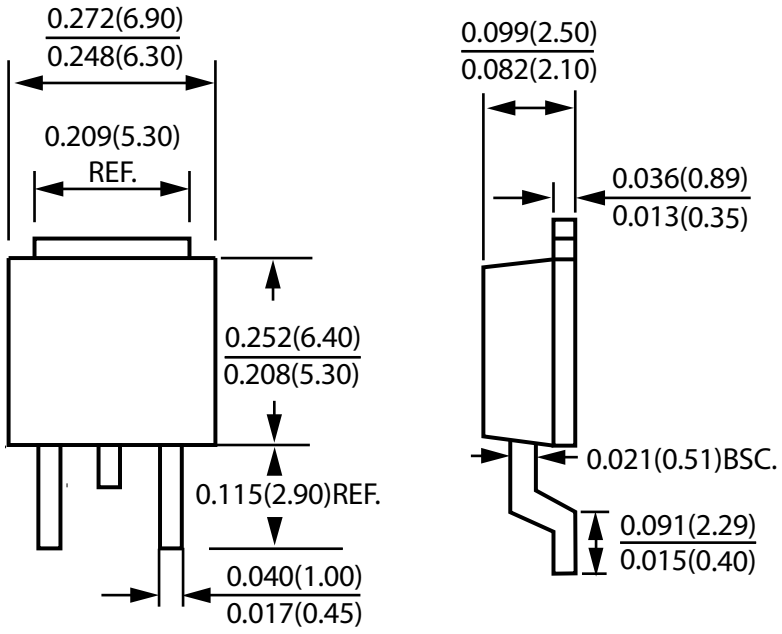


FIG. 6-Switching Time Waveform



Package Outline Dimensions



TO-252

Dimensions in inches and (millimeters)

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